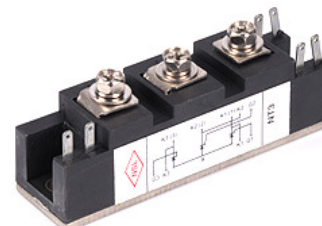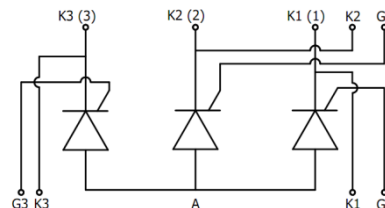# Non-isolated Thyristor Module, 60 Amps

Features

- Low voltage three-phase
- High surge current capability
- Easy construction
- Non-isolated
- Mounting base as common anode

Voltage Ratings (T_C = 25°C unless otherwise specified)				
Parameter	**Symbol**	**N3T60A30**	**N3T60A40**	**Units**
Maximum repetitive peak reverse voltage	V_{RRM}	300	400	V
Maximum non-repetitive peak reverse voltage	V_{RSM}	360	480	V
Maximum repetitive peak off-state voltage	V_{DRM}	300	400	V

Electrical Characteristics (T_C = 25°C unless otherwise specified)				
Parameter	**Conditions**	**Symbol**	**Values**	**Units**
Average on-state current	Single phase, half-wave, 180^0 conduction	$I_{T(AV)}$	60	A
R.M.S. on-state current		$I_{T(RMS)}$	94	A
On-state surge current	half cycle, 50Hz, peak value, non-repetitive	I_{TSM}	1800	A
I^2t required for fusing		I^2t	16200	A^2S
Peak gate current		I_{GM}	3	A
Peak gate voltage (forward)		V_{FGM}	10	V
Peak gate voltage (reverse)		V_{RGM}	5	V
Critical rate of rise of on-state current	I_G = 150mA, T_J=25^{0}C	di/dt	50	A/µs
Critical rate of rise of off-state voltage	T_J = 150^{0}C	dv/dt	50	V/µs
Holding current	T_J = 25^{0}C	I_H	100	mA
Peak on-state voltage	T_J = 25^{0}C	V_{TM}	1.25	V
Repetitive Peak Reverse Current	T_J = 150^{0}C, single phase, half wave	I_{RRM}	10	mA
Gate Trigger Current	T_J = 25^{0}C, I_T = 1A	I_{GT}	150	mA
Gate Trigger Voltage	T_J = 25^{0}C, I_T = 1A	V_{GT}	2	V

Thermal & Mechanical Specifications (T_C = 25°C unless otherwise specified)			
Parameter	**Symbol**	**Values**	**Units**
Operating junction temperature range	T_J	-40 to +150	^{0}C
Storage temperature range	T_{STG}	-40 to +125	^{0}C
Thermal resistance, junction to case	$R_{th(JC)}$	0.35	^{0}C/W
Weight	W	180	g

Package Outline

(All dimensions in mm)

Ordering Table

N3T	60	A	40
1	2		3

1 – Half-bridge Thyristor Module

2 - Current Rating = $I_{T(AV)}$

3 – Voltage = V_{RRM} (Voltage Ratings Table)